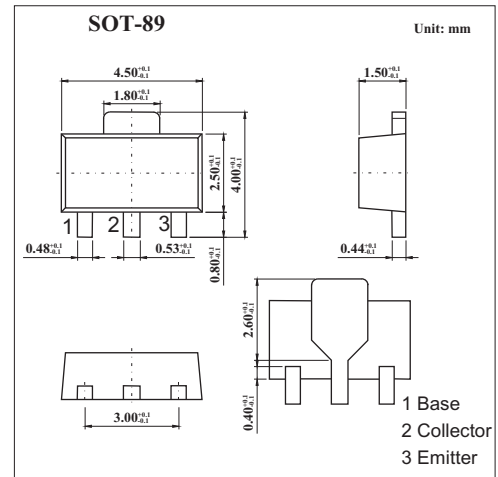


## Epitaxial Planar PNP Transistor

## KTA1668

## Features

Collector Power dissipation:  $P_c=500\text{mW}$ Collector Current -Continuous:  $I_c=-1\text{A}$ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current -Continuous	$I_c$	-1	A
Collector Power dissipation	$P_c$	500	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-1\text{mA}, I_E=0$	-80			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_c=-10\text{mA}, I_B=0$	-60			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_c=0$	-5.0			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-50\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-4\text{V}, I_B=0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE1}$	$V_{CE}=-2\text{V}, I_c=-0.05\text{A}$	60		200	
	$h_{FE2}$	$V_{CE}=-2\text{V}, I_c=-1\text{A}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=-500\text{mA}, I_B=-50\text{mA}$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c=-500\text{mA}, I_B=-50\text{mA}$			-1.2	V
Transition frequency	$f_T$	$V_{CE}=-10\text{V}, I_c=-0.05\text{A}$		150		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		12		pF